PATENT
81788.0026

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:
Seiichi MORI
Serial No: 09,456,873
Filed: December 8, 1999
For: NON-VOLATILE SEMICONDUCTOR MEMORY DEVICE

Art Unit: 2826
Examiner: Andujar, L.

413

I hereby certify that this correspondence is being facsimile transmitted to the United States Patent and Trademark Office, Fax No. 703 308 7722 on March 8, 2002.
Stephen R. Mason, Reg. No 41,179
Name
Signature
March 8, 2002
Date

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

Prior to the examination of the above-identified application, please enter the following amendments and remarks

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IN THE CLAIMS:

Rewrite claim 1 as follows:

1. A non-volatile semiconductor memory device comprising:

a semiconductor substrate; and

a memory cell having a floating gate provided through a tunnel insulating layer on said semiconductor substrate, and a control gate provided through an inter-layer insulating layer on said floating gate;

wherein said inter-layer insulating layer includes:

a silicon oxide layer contiguous to said floating gate;